

# Taw Kuei Chan

## List of Publications by Year in descending order

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29  
papers

599  
citations

687363

13  
h-index

580821

25  
g-index

30  
all docs

30  
docs citations

30  
times ranked

1203  
citing authors

#	ARTICLE	IF	CITATIONS
1	Ion induced intermixing and consequent effects on the leakage currents in HfO <sub>2</sub> /SiO <sub>2</sub> /Si systems. Applied Physics A: Materials Science and Processing, 2017, 123, 1.	2.3	14
2	Synthesis of embedded Au nanostructures by ion irradiation: influence of ion induced viscous flow and sputtering. Beilstein Journal of Nanotechnology, 2014, 5, 105-110.	2.8	15
3	Towards simultaneous achievement of carrier activation and crystallinity in Ge and GeSn with heated phosphorus ion implantation: An optical study. Applied Physics Letters, 2014, 105, 122108.	3.3	12
4	Single Crystalline Germanium-Lead Alloy on Germanium Substrate Formed by Pulsed Laser Epitaxy. ECS Solid State Letters, 2014, 3, P91-P93.	1.4	12
5	Germanium-lead alloy with 0.3% substitutional lead formed by pulsed laser induced epitaxy. , 2014, , .		0
6	Compositional dependence of optical critical point parameters in pseudomorphic GeSn alloys. Journal of Applied Physics, 2014, 116, 053520.	2.5	25
7	Loss of implanted heavy elements during annealing of ultra-shallow ion-implanted silicon: The complete picture. Applied Surface Science, 2014, 314, 322-330.	6.1	4
8	Ion beam studies of Hafnium based alternate high-k dielectric films deposited on silicon. Nuclear Instruments & Methods in Physics Research B, 2014, 332, 389-392.	1.4	14
9	Tuning the Interface Conductivity of LaAlO <sub>3</sub> /SrTiO <sub>3</sub> Using Ion Beams: Implications for Patterning. ACS Nano, 2013, 7, 10572-10581.	14.6	34
10	Ion beam-mixing effects in nearly lattice-matched AlInN/GaN heterostructures by swift heavy ion irradiation. Radiation Effects and Defects in Solids, 2012, 167, 506-511.	1.2	4
11	Magnetism in MoS <sub>2</sub> induced by proton irradiation. Applied Physics Letters, 2012, 101, .	3.3	205
12	Solid phase epitaxy of ultra-shallow Sn implanted Si observed using high-resolution Rutherford backscattering spectrometry. Applied Physics Letters, 2012, 101, 081602.	3.3	2
13	Formation of nanoclusters with varying Pb/Se concentration and distribution after sequential Pb <sup>+</sup> and Se <sup>+</sup> ion implantation into SiO <sub>2</sub> . Nuclear Instruments & Methods in Physics Research B, 2012, 273, 199-202.	1.4	6
14	Gradient inverse opal photonic crystals via spatially controlled template replication of self-assembled opals. Nanoscale, 2011, 3, 4951.	5.6	19
15	Mega-electron-volt proton irradiation on supported and suspended graphene: A Raman spectroscopic layer dependent study. Journal of Applied Physics, 2011, 110, .	2.5	56
16	Sub-100keV ion beam generation with a Van De Graaff accelerator using an external DC voltage supply. Nuclear Instruments & Methods in Physics Research B, 2011, 269, 2699-2702.	1.4	1
17	The effect of layer number and substrate on the stability of graphene under MeV proton beam irradiation. Carbon, 2011, 49, 1720-1726.	10.3	86
18	Reduced Contact Resistance and Improved Surface Morphology of Ohmic Contacts on GaN Employing KrF Laser Irradiation. Japanese Journal of Applied Physics, 2011, 50, 04DF06.	1.5	1

#	ARTICLE	IF	CITATIONS
19	Formation of epitaxial metastable NiGe <sub>2</sub> thin film on Ge(100) by pulsed excimer laser anneal. Applied Physics Letters, 2010, 97, .	3.3	20
20	Electrochemical Anodization of Silicon-on-Insulator Wafers Using an AC. Electrochemical and Solid-State Letters, 2010, 13, H271.	2.2	0
21	Lanthanide-based graded barrier structure for enhanced nanocrystal memory properties. Applied Physics Letters, 2009, 95, 113113.	3.3	3
22	HRBS/channeling studies of ultra-thin ITO films on Si. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 1464-1467.	1.4	3
23	Interface strain study of thin Lu <sub>2</sub> O <sub>3</sub> /Si using HRBS. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 1486-1489.	1.4	5
24	Realization of Silicon-Germanium-Tin (SiGeSn) Source/Drain Stressors by Sn implant and Solid Phase Epitaxy for strain engineering in SiGe channel P-MOSFETs. , 2008, , .		1
25	Lu <sub>2</sub> O <sub>3</sub> •Al <sub>2</sub> O <sub>3</sub> gate dielectrics for germanium metal-oxide-semiconductor devices. Applied Physics Letters, 2008, 93, 062901.	3.3	9
26	Structural, magnetic, and transport investigations of CrTe clustering effect in (Zn,Cr)Te system. Journal of Applied Physics, 2007, 102, .	2.5	14
27	Strained SiGeSn formed by Sn implant into SiGe and pulsed laser annealing. Applied Physics Letters, 2007, 91, 202105.	3.3	15
28	Channeling contrast microscopy of epitaxial lateral overgrowth of ZnO/GaN films. Nuclear Instruments & Methods in Physics Research B, 2007, 260, 299-303.	1.4	0
29	The CIBA high resolution RBS facility. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 915-917.	1.4	19